

MOSFETs Silicon N-Channel MOS (DTMOSIV)

TK20C60W

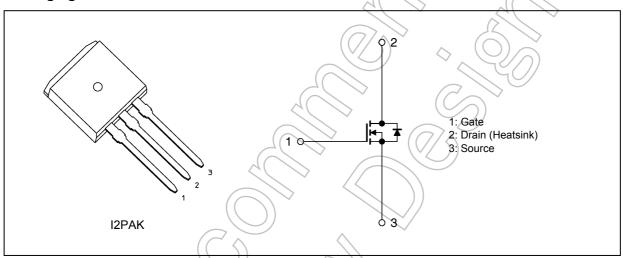
1. Applications

· Switching Voltage Regulators

2. Features

- (1) Low drain-source on-resistance: $R_{DS(ON)}$ = 0.13 Ω (typ.) by used to Super Junction Structure : DTMOS
- (2) Easy to control Gate switching
- (3) Enhancement mode: $V_{th} = 2.7$ to 3.7 V ($V_{DS} = 10$ V, $I_D = 1$ mA)

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) (Ta = 25°C unless otherwise specified)

Characteristics	Symbol	Rating	Unit	
Drain-source voltage		V _{DSS}	600	V
Gate-source voltage		V _{GSS}	±30	
Drain current (DC)	(Note 1)	I _D	20	Α
Drain current (pulsed)	(Note 1)	I _{DP}	80	
Power dissipation (T _c = 25°C)		P_{D}	165	W
Single-pulse avalanche energy	(Note 2)	E _{AS}	200	mJ
Avalanche current		I _{AR}	5	Α
Reverse drain current (DC)	(Note 1)	I _{DR}	20	
Reverse drain current (pulsed)	(Note 1)	I _{DRP}	80]
Channel temperature		T _{ch}	150	°C
Storage temperature		T _{stg}	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production



5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal resistance	R _{th(ch-c)}	0.757	°C/W
Channel-to-ambient thermal resistance	R _{th(ch-a)}	83.3	

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: V_{DD} = 90 V, T_{ch} = 25°C (initial), L = 14 mH, R_{G} = 25 $\Omega,\,I_{AR}$ = 5 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.





6. Electrical Characteristics

6.1. Static Characteristics (T_a = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±1	μΑ
Drain cut-off current	I _{DSS}	V _{DS} = 600 V, V _{GS} = 0 V		_	10	
Drain-source breakdown voltage	V _{(BR)DSS}	I _D = 10 mA, V _{GS} = 0 V	600	_	_	V
Gate threshold voltage	V_{th}	V _{DS} = 10 V, I _D = 1 mA	2.7) }	3.7	
Drain-source on-resistance	R _{DS(ON)}	V _{GS} = 10 V, I _D = 10 A		0.13	0.155	Ω

6.2. Dynamic Characteristics (T_a = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = 300 V, V _{GS} = 0 V, f = 1 MHz	_	1680		pF
Reverse transfer capacitance	C_{rss}	4(>>	_	N/	4	
Output capacitance	C _{oss}		- 1	40		
Effective output capacitance	C _{o(er)}	V _{DS} = 0 to 400 V, V _{GS} = 0 V	_((70		
Gate resistance	r _g	V _{DS} = OPEN, f = 1 MHz	K	(1.5)) —	Ω
Switching time (rise time)	t _r	See Figure 6.2.1		25		ns
Switching time (turn-on time)	t _{on}			50		
Switching time (fall time)	t _f		/ _/ _//	6		
Switching time (turn-off time)	t _{off}	$ (\bigcirc) \qquad (\bigcirc) $		100		
MOSFET dv/dt ruggedness	dv/dt	$V_{DD} = 0$ to 400 V, $I_D = 5$ A	50	_		V/ns

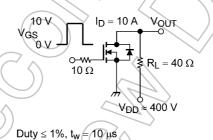


Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics ($T_a = 25^{\circ}$ C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$		48		nC
Gate-source charge 1	Q _{gs1}		_	11		
Gate-drain charge	Q_{gd}		_	22	_	

6.4. Source-Drain Characteristics (T_a = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	V_{DSF}	I _{DR} = 20 A, V _{GS} = 0 V	_	_	-1.7	V
Reverse recovery time	t _{rr}	I _{DR} = 10 A, V _{GS} = 0 V -dI _{DR} /dt = 50 A/µs		330	_	ns
Reverse recovery charge	Q_{rr}		_	2.9	_	μС
Peak reverse recovery current	I _{rr}		_	16	_	Α
Diode dv/dt ruggedness	dv/dt	I _{DR} = 10 A, V _{GS} = 0 V, V _{DD} = 400 V	15		_	V/ns

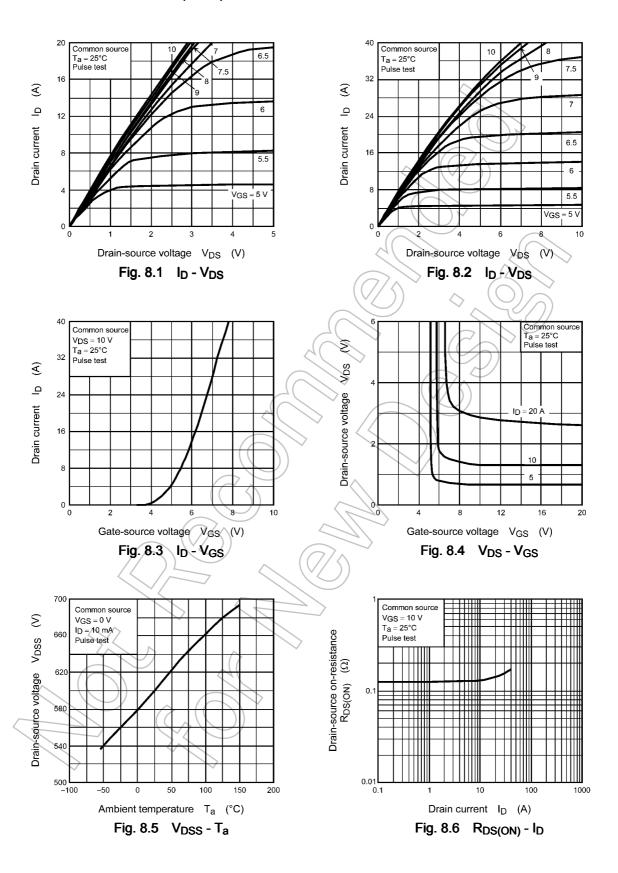


7. Marking



Rev.5.0

8. Characteristics Curves (Note)



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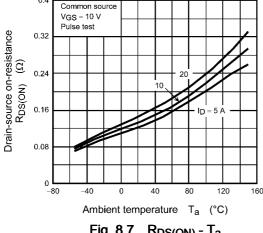
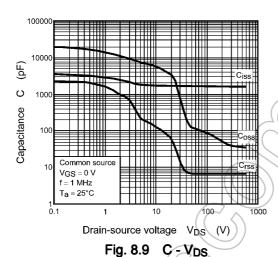


Fig. 8.7 R_{DS(ON)} - T_a



3 **#** threshold voltage Common source VDS = 10 V ID = 1 mA Ambient temperature T_a (°C)

Fig. 8.11 V_{th} - T_a

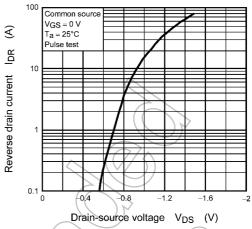


Fig. 8.8 IDR - VDS

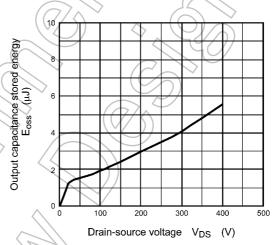


Fig. 8.10 Eoss - V_{DS}

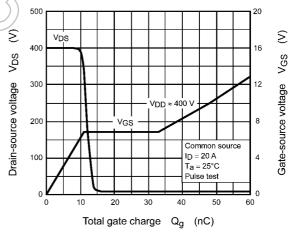


Fig. 8.12 Dynamic Input/Output Characteristics

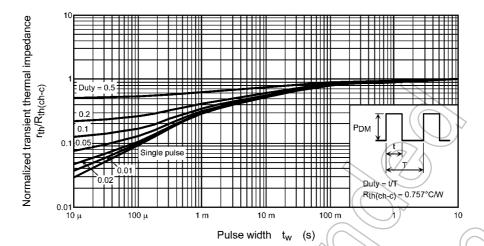


Fig. 8.13 r_{th} - t_w (Guaranteed Maximum)

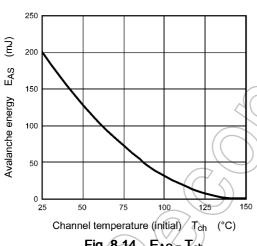


Fig. 8.14 E_{AS} - T_{ch} (Guaranteed Maximum)

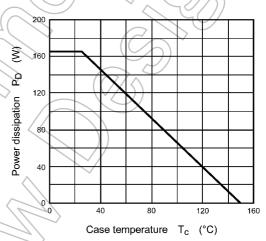


Fig. 8.15 P_D - T_c (Guaranteed Maximum)

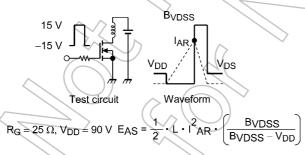


Fig. 8.16 Test Circuit/Waveform

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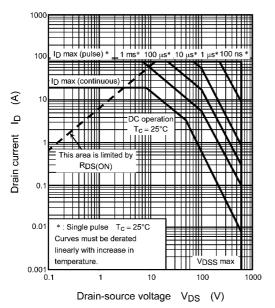


Fig. 8.17 Safe Operating Area (Guaranteed Maximum)

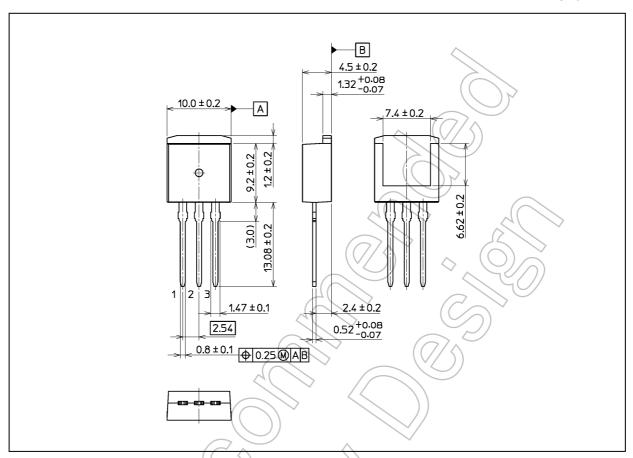
Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



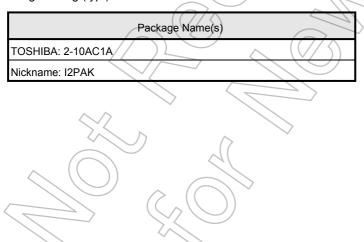


Package Dimensions

Unit: mm



Weight: 1.6 g (typ.)





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